**Product Specification** 1000.428601 Issue Date 24 April 2015 14:28:2

Part Number	Customer	
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Icemos Technology Ltd

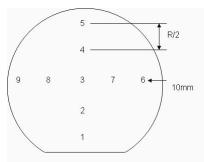
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	Wafer Vendor
	5.0	Overall Thickness	350.00 +/- 12.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	300.00 +/- 10.00 μm	ADE, 100%
	14.0	Handle Doping Type	Р	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.001 - 0.01 Ohmem	Wafer Vendor
	17.0	Backside Finish	Polished with laser marking	Guaranteed by process
BuriedOxide	18.0	Oxide Type	NONE	Guaranteed by process
DeviceSilicon	21.0	Device Growth Method	FZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	23.0	Nominal Thickness	50.00 +/- 2.00 μm	FTIR 9 point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by process
	25.0	Device Doping Type	Р	Wafer Vendor
	26.0	Device Dopant	Boron	Wafer Vendor
	27.0	Device Resistivity	6000 - 12000 Ohmem	Wafer Vendor
	28.0	Buried Layer Implant	None	Guaranteed by process
	29.0	Voids	0	Bright Light, 100% (note 2)
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	ction performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information

Icemos Technology Ltd